



**ZXTN4240F** 

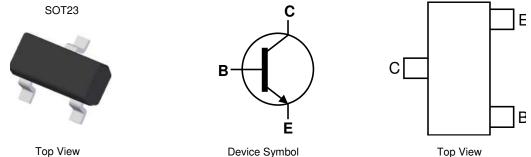
#### 40V NPN LOW SATURATION TRANSISTOR IN SOT23

### Features

- BV<sub>CEO</sub> > 40V
- I<sub>C</sub> = 2A high Continuous Collector Current
- I<sub>CM</sub> = 3A Peak Pulse Current
- Low Saturation Voltage 180mV Max @  $I_C = 1A$
- $R_{CE(SAT)} = 60m\Omega$  at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary PNP Type: ZXTP5240F
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.008 grams (Approximate)



Pin Configuration

## Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTN4240F-7	2D4	7	8	3,000

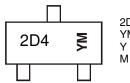
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



2D4= Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code K	ey											
Year	2017	2018	2019	2020	2021	2022	202	23 20	024	2025	2026	2027
Code	E	F	G	Н		J	K		L	М	Ν	0
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Peak Pulse Collector Current	Ісм	3	А
Continuous Collector Current	Ι <sub>C</sub>	2	А
Peak Base Current	I <sub>BM</sub>	0.3	А

## **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	730	mW
Power Dissipation (Note 6)	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R <sub>0JA</sub>	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	R <sub>θJA</sub>	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R <sub>θJL</sub>	75	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

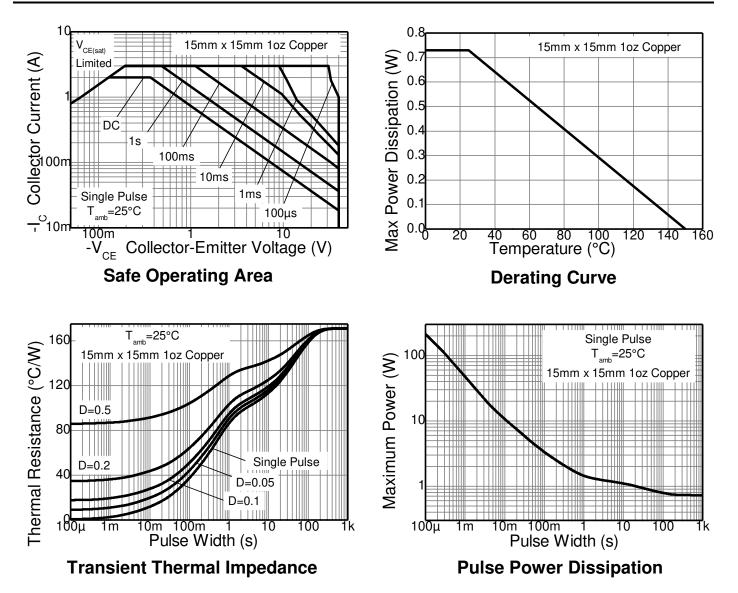
## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under 5. For a device mounted with the collector lead on 15mm X 15mm 102 copper that is on a s still air conditions whilst operating in a steady-state.
 6. Same as note (5), except the device is mounted on minimum recommended pad layout.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**



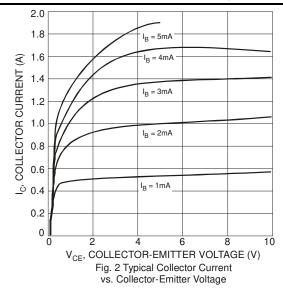


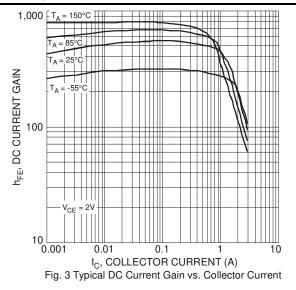
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

			I		1	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	40			V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	40			V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5		_	V	I <sub>E</sub> = 100μA
Collector-Base Cutoff Current	l		_	100	nA	$V_{CB} = 30V, I_E = 0$
	I <sub>СВО</sub>			50	μA	$V_{CB} = 30V, I_E = 0, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>		_	100	nA	$V_{EB} = 4V, I_C = 0$
ON CHARACTERISTICS (Note 8)						
		350		_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	h	300				$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h <sub>FE</sub>	300		_		$V_{CE} = 2V, I_C = 1A$
		150				$V_{CE} = 2V, I_C = 2A$
		_		70		$I_{C} = 100 \text{mA}, I_{B} = 1 \text{mA}$
	V <sub>CE(SAT)</sub>	_	30	100	mV	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Collector-Emitter Saturation Voltage		_	_	180		I <sub>C</sub> = 750mA, I <sub>B</sub> = 15mA
		_		180		$I_{C} = 1A, I_{B} = 50mA$
			_	320		$I_{\rm C} = 2A, I_{\rm B} = 200 {\rm mA}$
Equivalent On-Resistance	R <sub>CE(SAT)</sub>		60	200	mΩ	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_		1.1	V	$I_{\rm C} = 2A, I_{\rm B} = 200 {\rm mA}$
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>	_		0.75	V	$V_{CE} = 2V, I_{C} = 100 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f <sub>T</sub>	100	—	_	MHz	$\label{eq:VCE} \begin{array}{l} V_{CE} = 10V, \ I_C = 100mA, \\ f = 100MHz \end{array}$
Output Capacitance	C <sub>OB</sub>	_		20	pF	V <sub>CB</sub> = 10V, f = 1MHz
Turn-On Time	t <sub>ON</sub>	_	43	_	ns	I <sub>C</sub> =500mA, V <sub>CC</sub> =10V,
Turn-Off Time	toFF	_	363	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

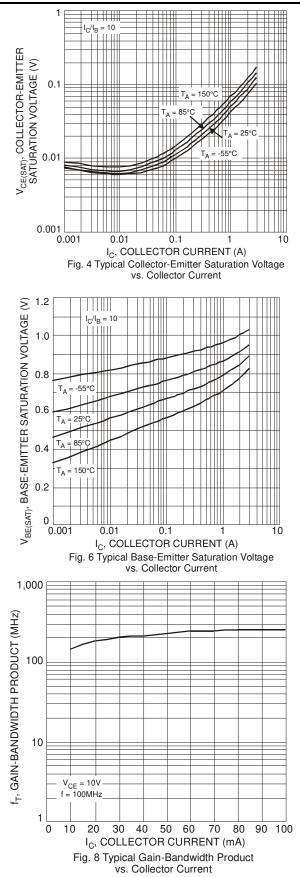
# **Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

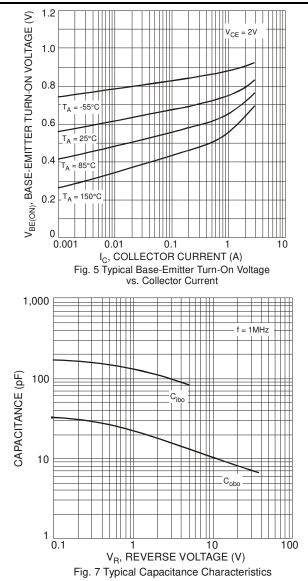






# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.) (Continued)

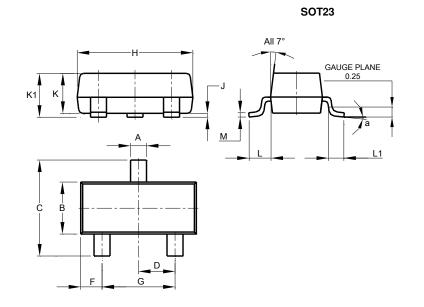






# **Package Outline Dimensions**

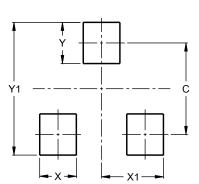
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
H	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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